AMENDMENT TO THE CLAIMS

In the Claims

Please **CANCEL** claims 8-16, 19 and 25-32; and

Please **AMEND** claims 33 and 34 as follows:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-16 (Canceled).

17. (Previously Presented) A method of enhancing stress in a semiconductor device, comprising:

depositing a layer of nitride film over a gate stack and a surface of a substrate;

removing the nitride film on the gate stack to provide enhanced stress in a transistor channel under the gate stack;

forming a spacer adjacent a sidewall of the gate stack; and

etching upper portions of the spacer to form sidewalls only at a lower portion of the gate stack.

Claims 18-32 (Canceled).

33. (Currently Amended) ~~The method of claim 8, further comprising~~ A method of enhancing stress in a semiconductor device, comprising:

depositing a layer of nitride film over a gate stack and a surface of a substrate;

removing the nitride film on the gate stack to provide enhanced stress in a transistor channel under the gate stack; and

depositing a salicide gate region on top of the gate stack,

wherein a gate is about 60 nm wide, a spacer is about 50 nm wide, and the nitride film provides a stress of about 2.0 GPa, the enhanced stress in the transistor channel is greater than approximately 4.5×10^9 dynes/cm^2 at about 5 nm below a gate oxide.

34. (Currently Amended) ~~The method of claim 8,~~ A method of enhancing stress in a semiconductor device, comprising:

depositing a layer of nitride film over a gate stack and a surface of a substrate; and

removing the nitride film on the gate stack to provide enhanced stress in a transistor channel under the gate stack,

wherein a gate is about 60 nm wide, a spacer is about 50 nm wide, and the nitride film provides a stress of about 2.0 GPa, the enhanced stress in the transistor channel is greater than approximately 4.5×10^9 dynes/cm^2 at about 5 nm below a gate oxide, and

wherein the substrate remains covered by the nitride film after the nitride film is removed from an upper portion of the gate stack.